

# Device Modeling Report

COMPONENTS: BRT  
PART NUMBER: RN1105FT  
MANUFACTURER: TOSHIBA

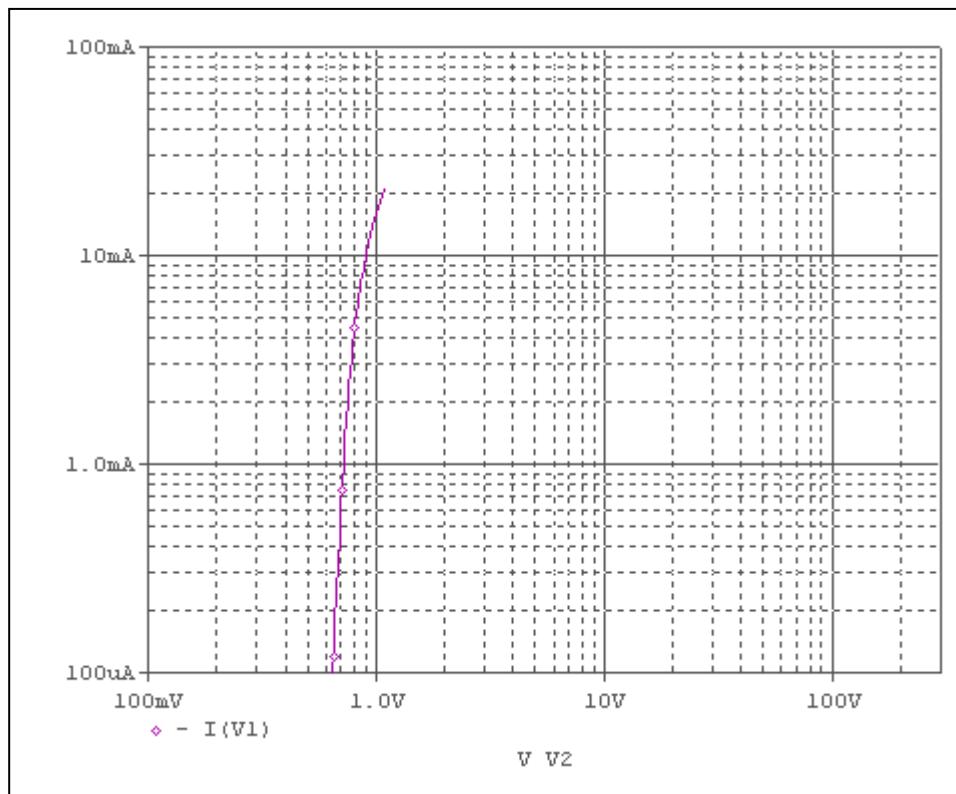


Bee Technologies Inc.

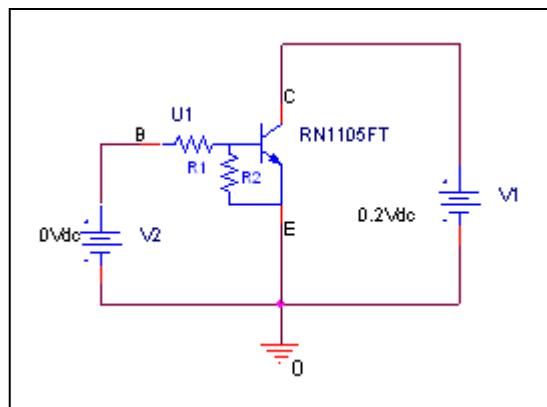
PSpice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
NF	Forward Current Emission Coefficient
VAF	Forward Early Voltage
IKF	Forward Beta Roll-off Knee Current
ISE	Non-ideal Base-Emitter Diode Saturation Current
NE	Non-ideal Base-Emitter Diode Emission Coefficient
BR	Ideal Maximum Reverse Beta
NR	Reverse Emission Coefficient
VAR	Reverse Early Voltage
IKR	Reverse Beta Roll-off Knee Current
ISC	Non-ideal Base-Collector Diode Saturation Current
NC	Non-ideal Base-Collector Diode Emission Coefficient
NK	Forward Beta Roll-off Slope Exponent
RE	Emitter Resistance
RB	Base Resistance
RC	Series Collector Resistance
CJE	Zero-bias Emitter-Base Junction Capacitance
VJE	Emitter-Base Junction Potential
MJE	Emitter-Base Junction Grading Coefficient
CJC	Zero-bias Collector-Base Junction Capacitance
VJC	Collector-base Junction Potential
MJC	Collector-base Junction Grading Coefficient
FC	Coefficient for Onset of Forward-bias Depletion Capacitance
TF	Forward Transit Time
XTF	Coefficient for TF Dependency on Vce
VTF	Voltage for TF Dependency on Vce
ITF	Current for TF Dependency on Ic
PTF	Excess Phase at $f=1/2\pi * TF$
TR	Reverse Transit Time
EG	Activation Energy
XTB	Forward Beta Temperature Coefficient
XTI	Temperature Coefficient for IS

## Input voltage vs. output current (ON characteristics)

Circuit simulation result

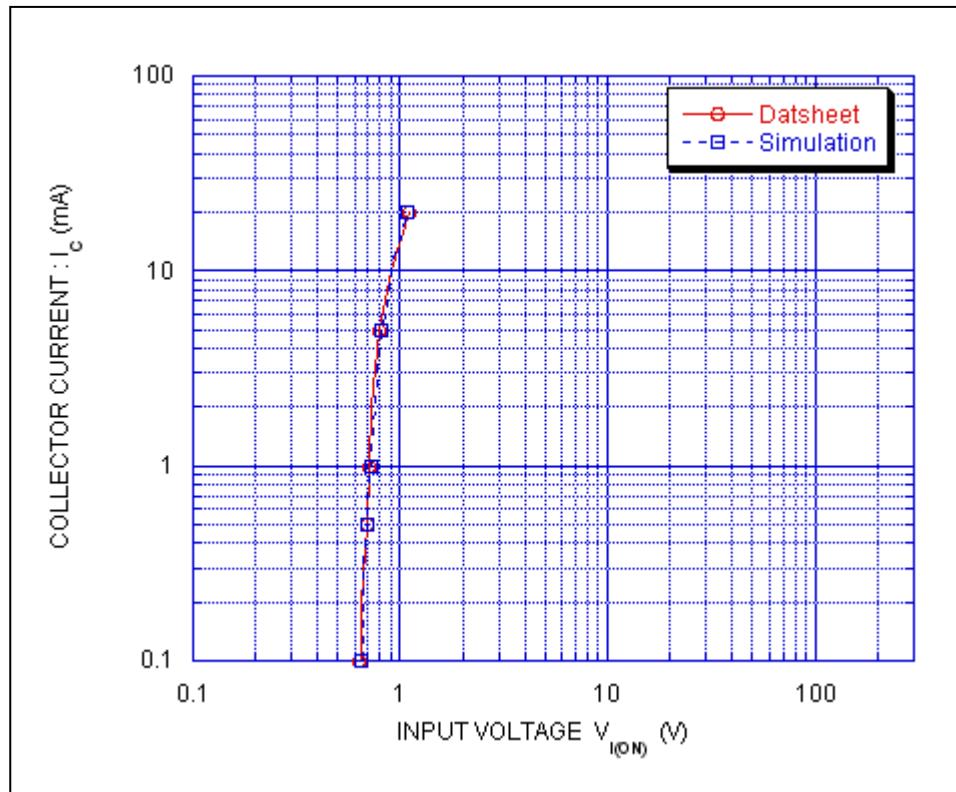


Evaluation circuit



## Comparison Graph

Circuit Simulation Result



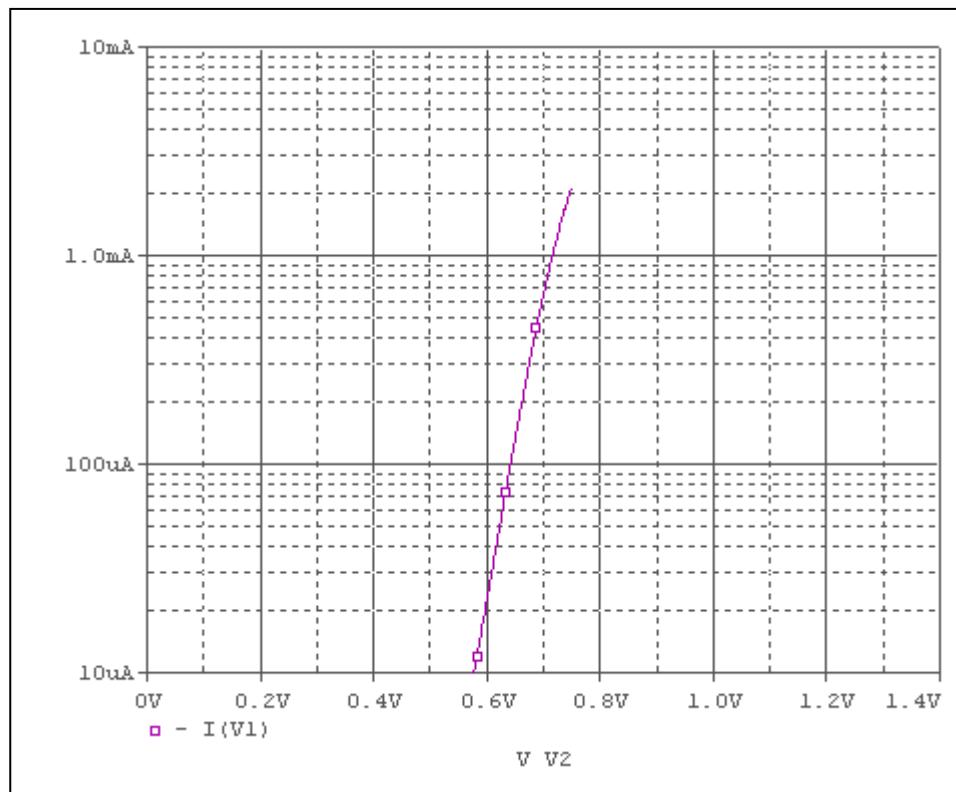
Simulation Result

Condition @  $V_{ce} = 0.2$  V

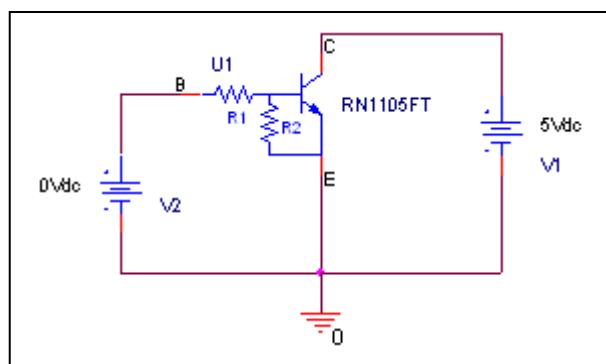
$I_c$ (mA)	$V_{I(ON)}$ (V)		Error (%)
	Datasheet	Simulation	
0.1	0.63	0.643412	2.1289
0.2	0.65	0.664595	2.2454
0.5	0.69	0.693361	0.4871
1	0.71	0.718763	1.2342
2	0.73	0.751454	2.9389
5	0.8	0.815396	1.9245
10	0.9	0.902974	0.3304
20	1.1	1.0826	1.5818

## Output current vs. input voltage (OFF characteristics)

Circuit simulation result

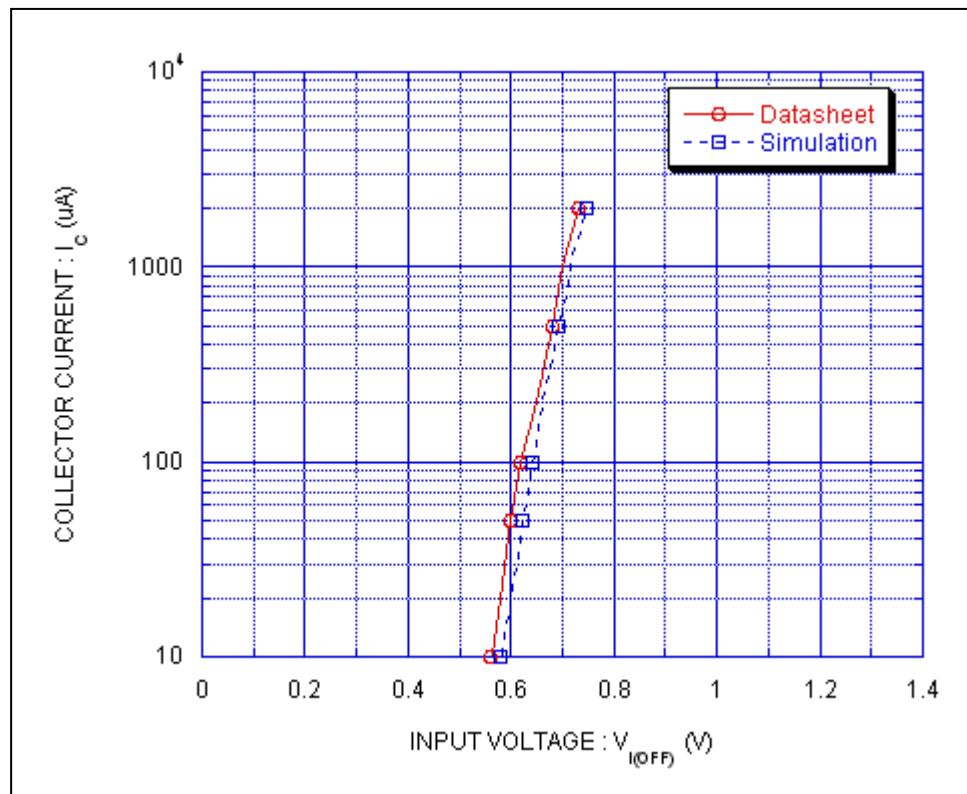


Evaluation circuit



## Comparison Graph

Circuit Simulation Result



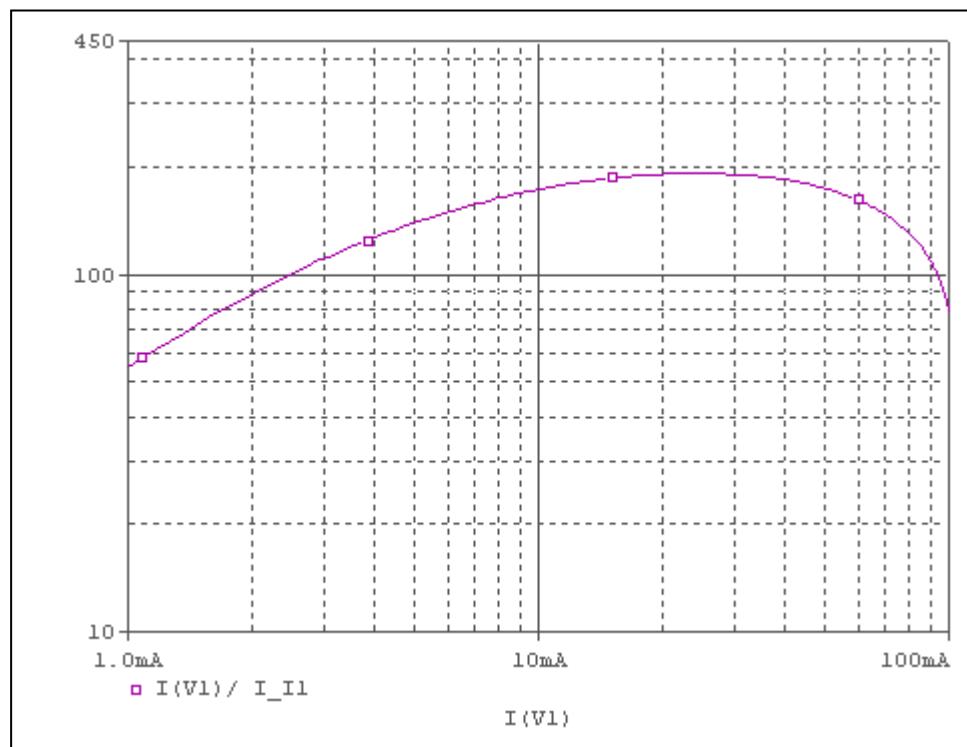
Simulation Result

Condition @  $V_{ce} = 5 \text{ V}$

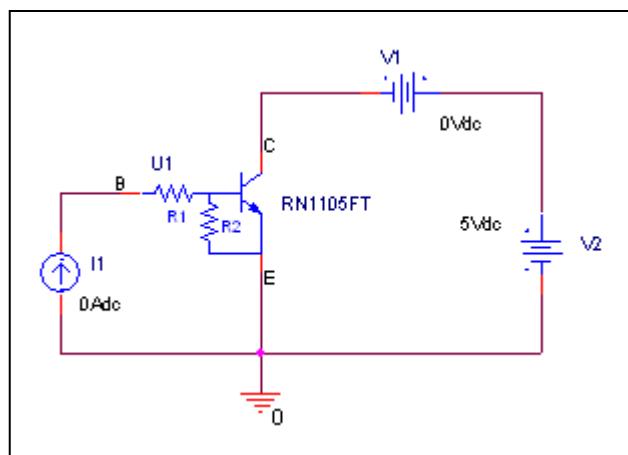
$I_c(\mu\text{A})$	$V_{I(OFF)} (\text{V})$		Error (%)
	Datasheet	Simulation	
10	0.56	0.577979	3.2105
20	0.58	0.597498	3.0169
50	0.6	0.622663	3.7772
100	0.62	0.642198	3.5803
200	0.65	0.662802	1.9695
500	0.68	0.691086	1.6303
1000	0.7	0.715822	2.2603
2000	0.73	0.746342	-2.2386

## DC current gain vs. output current

Circuit simulation result

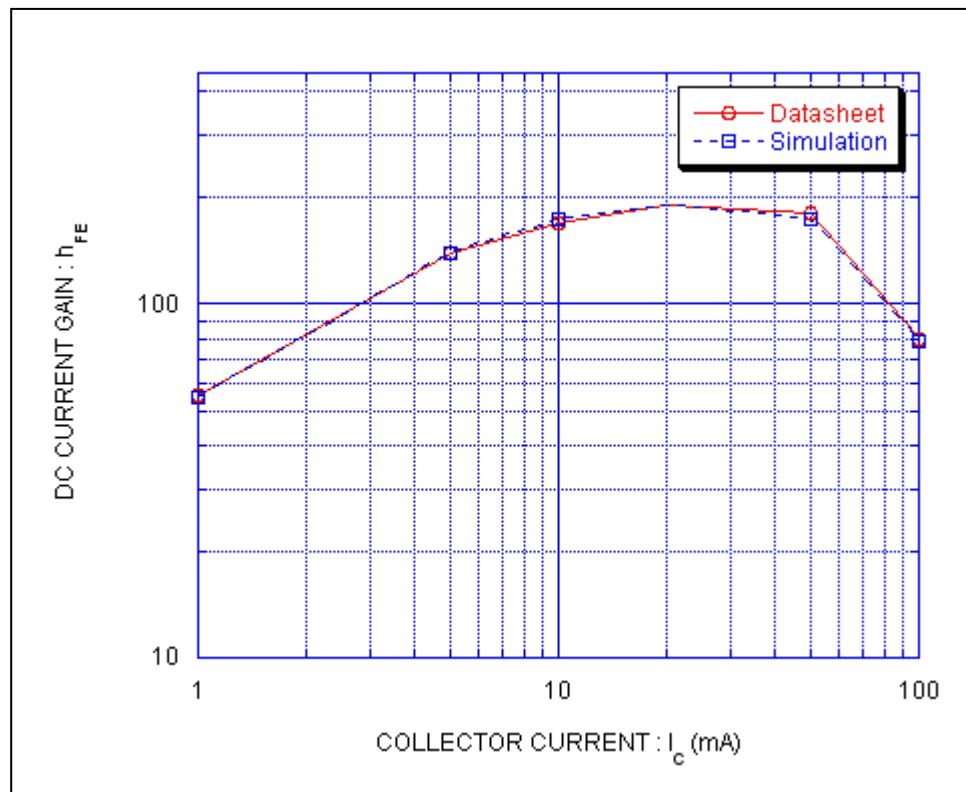


Evaluation circuit



## Comparison Graph

Circuit Simulation Result



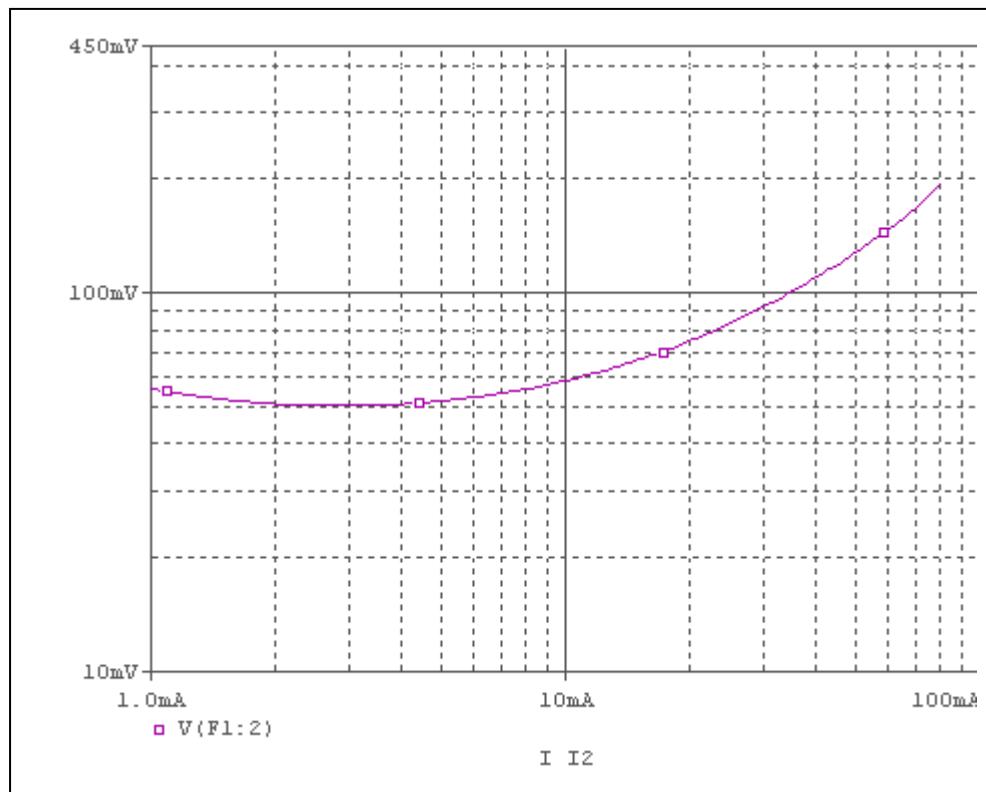
Simulation Result

Condition @  $V_{ce} = 5$  V

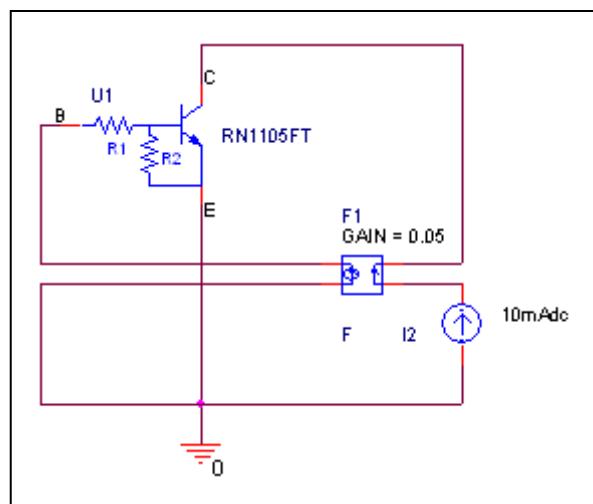
$I_c$ (mA)	hFE		Error (%)
	Datasheet	Simulation	
1	55	54.702	-0.5418
5	140	139.793	-0.1479
10	170	173.044	1.7906
20	190	190.613	0.3226
50	180	173.726	-3.4856
100	80	78.762	-1.5475

## Output voltage VS. output current

Circuit simulation result

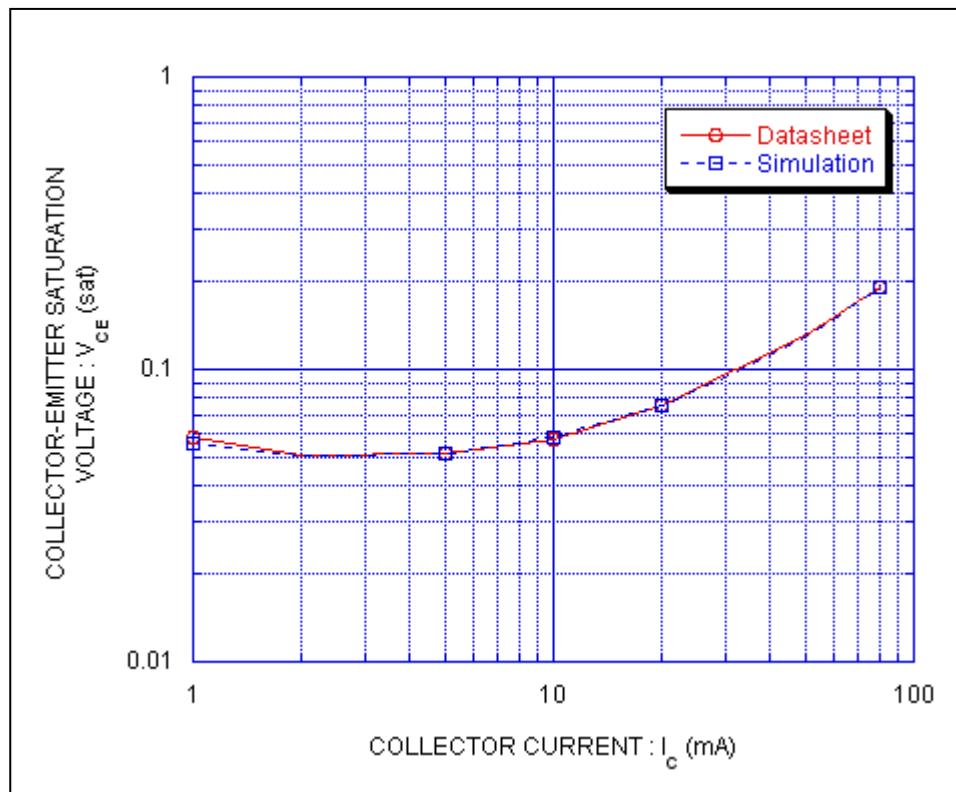


Evaluation circuit



## Comparison Graph

Circuit Simulation Result



Simulation Result

Condition @  $I_C/I_B = 20$

$I_C(\text{mA})$	$V_{CE(\text{sat})} (\text{mV})$		Error (%)
	Datasheet	Simulation	
1	0.059	0.056068	-4.9695
2	0.051	0.050965	-0.0686
5	0.052	0.051880	-0.2308
10	0.058	0.058646	1.1138
20	0.075	0.074748	-0.3360
50	0.13	0.128101	-1.4608
80	0.19	0.191879	0.9889